

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	677	(field adj oxide or fox or sti or (trench or groove or grooved) near (dielectric or insulating or insulation or isolating or isolation)) near5 (under or underneath or below or beneath or underlying or within or lower or bottom) near4 (implant or implantation or implanted or implanting or latch-up or leakage near stop or latching or latchup)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 09:56
L2	388	(nmos or pmos or nmosfet or pmosfet or cmos) and (field adj oxide or fox or sti or (trench or groove or grooved) near (dielectric or insulating or insulation or isolating or isolation)) near3 (under or underneath or below or beneath or underlying or within or bottom) near3 (implant or implantation or implanted or implanting or doped or dopant or doping)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 09:57
L3	229	(nmos or pmos or nmosfet or pmosfet or cmos) and (field adj oxide or fox or sti or (trench or groove or grooved) near (dielectric or insulating or insulation or isolating or isolation)) near3 (under or underneath or below or beneath or underlying or within or bottom) near3 (implant or implantation or implanted or implanting or doped or dopant or doping) and (leakage or leaking or latchup or latching or latch-up)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 11:57
L4	84	(nmos or pmos or nmosfet or pmosfet or cmos) and (field adj oxide or fox or sti or (trench or groove or grooved) near (dielectric or insulating or insulation or isolating or isolation)) near3 (align or aligned or aligning or alignment) near3 (implant or implantation or implanted or implanting or doped or dopant or doping)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 10:25
L5	243	(nmos or pmos or nmosfet or pmosfet or cmos) and (field adj oxide or fox or sti or (trench or groove or grooved) near (dielectric or insulating or insulation or isolating or isolation)) near3 (sidewall or side or wall or spacer) near5 (implant or implantation or implanted or implanting or doped or dopant or doping)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 11:17
L6	51	(nmos or pmos or nmosfet or pmosfet or cmos) and (implant or implanting or implanted) near2 (latchup or latch-up or latching or leakage near2 charge or leakage near2 current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 11:58
L7	82	(nmos or pmos or nmosfet or pmosfet or cmos) and (doped or doping) near2 (latchup or latch-up or latching or leakage near2 charge or leakage near2 current)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 11:04
L8	13	(nmos or pmos or nmosfet or pmosfet or cmos) and (field adj oxide or fox or sti or (trench or groove or grooved) near (dielectric or insulating or insulation or isolating or isolation)) with (junction or pn) near3 (control or controlling or controlled or positioning or positioned)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 11:23
L9	17	(nmos or pmos or nmosfet or pmosfet or cmos) and (field adj oxide or fox or sti or (trench or groove or grooved) near (dielectric or insulating or insulation or isolating or isolation)) with (aligned or alignment or position or positioned or aligning or positioning) near4 (center or halfway or middle or half)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 11:24
L10	28	(nmos or pmos or nmosfet or pmosfet or cmos) and (implant or implanting or implanted) near2 (latchup or latch-up or latching or leakage or conduction near channel) with (isolation or groove or trench or sti or isolating or fox or field adj oxide or buried adj oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 11:59
L14	91	(nmos or pmos or nmosfet or pmosfet or cmos) and (field adj oxide or fox or sti or (trench or groove or grooved) near (dielectric or insulating or insulation or isolating or isolation)) near3 (under or underneath or below or beneath or underlying or within or bottom) near3 (implant or implantation or implanted or implanting or doped or dopant or doping) and (punch-thru or punch-through or punchthru or punchthrough)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 11:58

L15	612	(nmos or pmos or nmosfet or pmosfet or cmos) and (implant or implanting or implanted) near2 (punchthrough or punch-thru or punch-through or punchthru)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 11:58
L16	55	(nmos or pmos or nmosfet or pmosfet or cmos) and (implant or implanting or implanted) near2 (punchthrough or punchthru or punch-through or punch-thru) with (isolation or groove or trench or sti or isolating or fox or field adj oxide or buried adj oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 12:27
L17	22	"6054344".pn. "6033949".pn. "5861330".pn. "6342429".pn. "6313011".pn. "6228726".pn. "5770504".pn. "6177333".pn. "6069057".pn. "6248645".pn. "6472301".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 12:30